IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Alexei Sadovnikov

Application No.: New

Filed: Herewith

For: LOW DOPED BASE SPACER FOR REDUCTION OF EMITTER-BASE CAPACITANCE IN BIPOLAR TRANSISTORS WITH SELECTIVELY GROWN EPITAXIAL BASE

Group Art Unit: Unknown

Examiner: Unknown

INFORMATION DISCLOSURE STATEMENT

121 Spear Street, Suite 290 San Francisco, CA 94105 (415) 512-1312

Mail Stop PATENT APPLICATION Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

		ILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope, addressed to: Commissioner for Patents, Washington, DC 20231 on September 23, 2003.

STALLMAN & POLLOCK LLP

Dated: 09/23/03

Lana T. Brenner

Sir:

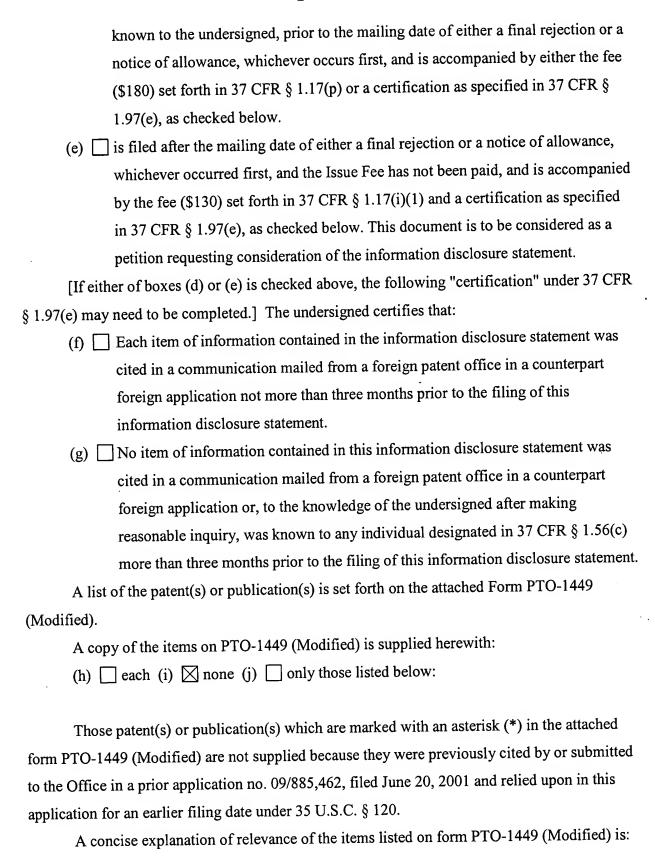
Applicant(s) submit(s) herewith patents, publications or other information [attached hereto and listed on the attached Form PTO-1449 (modified)] of which he is aware, which he believe(s) may be material to the examination of this application and in respect of which there may be a duty to disclose in accordance with 37 CFR § 1.56.

This Information Disclosure Statement:

(a) accompanies the new patent application submitted herewith. 37 CFR § 1.97(a).
(b) is filed within three months after the filing date of the application or within three months after the date of entry of the national stage of a PCT application as set forth in 37 CFR § 1.491.
(c) as far as is known to the undersigned, is filed before the mailing date of a first Office Action on the merits.
(d) is filed after the first office action and more than three months after the

application's filing date or PCT national stage date of entry filing but, as far as is

Atty Docket No.: NSC1-H2610 [P04882 D1]



Atty Docket No.: NSC1-H2610 [P04882 D1]

(k) \(\sum \) not given

(1)	given for each listed item
(m)	given for only non-English language listed item(s) [Required]
(n)	is in the form of an English language copy of a Search Report from a foreign
	patent office, issued in a counterpart application, which refers to the relevant
	portions of the references [copy attached].

The Examiner is reminded that a "concise explanation of the relevance" of the submitted items "may be nothing more than identification of the particular figure or paragraph of the patent or publication which has some relation to the claimed invention," MPEP § 609.

While the information and references disclosed in this Information Disclosure Statement may be "material" pursuant to 37 CFR § 1.56, it is not intended to constitute an admission that any patent, publication or other information referred to therein is "prior art" for this invention unless specifically designated as such.

In accordance with 37 CFR § 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 CFR § 1.56(a) exists. It is submitted that the Information Disclosure Statement is in compliance with 37 CFR § 1.98 and MPEP § 609 and the Examiner is respectfully requested to consider the listed references.

Respectfully submitted,

STALLMAN & POLLOCK LLP

Dated: September 23, 2003

Michael J. Pollock

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Attorneys for Applicant(s)

Atty Docket No.: NSC1-H2610 [P04882 D1]

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional) NSC1-H2610	Application Number New		
Applicant(s) Alexei Sadovnikov			
Filing Date	Group Art Unit		
Herewith	Unknown		

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	Ref	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE
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	*AB	2003/0001235 A1	01/02/03	Hashimoto	257	592	08/29/02
	*AC	5,494,836	02/27/96	Imai	437	31	06/02/95
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REF	NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	YES	No
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(Including Author, Title, Date, Pertinent Pages, Etc.)

	*AO	A. Schuppen et al. "Enhanced SiGe Heterojunction Bipolar Transistors with 160 GHz-f _{max} ", IEDM 95 743-746, 1995 IEEE.
	*AR	Denny D. Tang, "A Reduced-Field Design Concept for High-Performance Bipolar Transistors", IEEE Electron Device Letters, Vol. 10, No. 2, February 1989, pp 67-69.
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MPEP Section 609; Draw line through citation if ation to applicant.
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